

MA3S133

Silicon epitaxial planar type

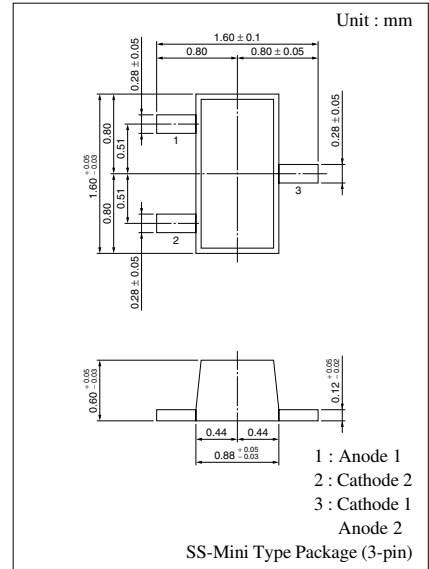
For switching circuits

■ Features

- Super-small SS-mini type package contained two elements, allowing high-density mounting
- Two diodes are connected in series in the package

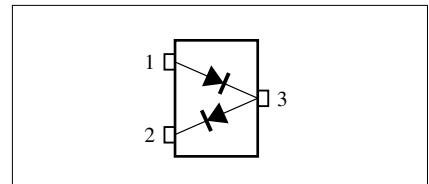
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|----------------------|-----------|-------------|------------------|
| Reverse voltage (DC) | V_R | 80 | V |
| Peak reverse voltage | V_{RM} | 80 | V |
| Forward current (DC) | Single | I_F | mA |
| | Series | | |
| Peak forward current | Single | I_{FM} | mA |
| | Series | | |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |



Marking Symbol: MP

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-------------------------------------|---------------|---|-----|-----|-----|------|
| Reverse current (DC) | I_R | $V_R = 75\text{ V}$ | | | 100 | nA |
| Forward voltage (DC) | V_F | $I_F = 100\text{ mA}$ | | | 1.2 | V |
| Reverse voltage (DC) | V_R | $I_R = 100\ \mu\text{A}$ | 80 | | | V |
| Terminal capacitance | C_t^{*1} | $V_R = 0\text{ V}, f = 1\text{ MHz}$ | | | 5.5 | pF |
| | C_t^{*2} | $V_R = 0\text{ V}, f = 1\text{ MHz}$ | | | 3.0 | pF |
| Reverse recovery time ^{*3} | t_{rr}^{*1} | $I_F = 10\text{ mA}, V_R = 6\text{ V}$ $I_{tr} = 0.1 \cdot I_R, R_L = 100\ \Omega$ | | 150 | | ns |
| | t_{rr}^{*2} | $I_F = 10\text{ mA}, V_R = 6\text{ V}$ $I_{tr} = 0.1 \cdot I_R, R_L = 100\ \Omega$ | | 9 | | ns |

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Between pins 2 and 3

*2 : Between pins 1 and 3

*3 : t_{rr} measuring circuit

